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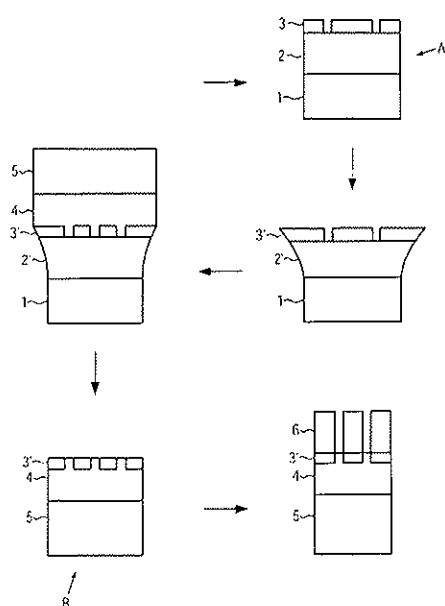


FIG. 1

(57) Abstract: The present invention relates a method for the formation of at least partially relaxed strained material on a target substrate, comprising the subsequently performed steps of forming islands from a strained material layer on an intermediate substrate, at least partially relaxing the strained material islands by a first heat treatment and transferring the at least partially relaxed strained material islands to the target substrate.



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